Preferred Device

Dual Schottky Barrier Diodes

Application circuit designs are moving toward the consolidation of device count and into smaller packages. The new SOT-363 package is a solution which simplifies circuit design, reduces device count, and reduces board space by putting two discrete devices in one small six-leaded package. The SOT-363 is ideal for low-power surface mount applications where board space is at a premium, such as portable products.

Surface Mount Comparisons:

	SOT-363	SOT-23
Area (mm ²)	4.6	7.6
Max Package P _D (mW)	120	225
Device Count	2	1

Space Savings:

Package	1 × SOT-23	$2 imes extsf{SOT-23}$		
SOT-363	40%	70%		

The MBD110DW, MBD330DW, and MBD770DW devices are spin-offs of our popular MMBD101LT1, MMBD301LT1, and MMBD701LT1 SOT-23 devices. They are designed for high-efficiency UHF and VHF detector applications. Readily available to many other fast switching RF and digital applications.

Features

- Extremely Low Minority Carrier Lifetime
- Very Low Capacitance
- Low Reverse Leakage
- Pb-Free Packages are Available

MAXIMUM RATINGS

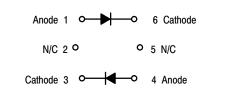
Rati	Symbol	Value	Unit	
Reverse Voltage	MBD110DWT1 MBD330DWT1 MBD770DWT1	V _R	7.0 30 70	V
Forward Power Dissip	P _F	120	mW	
Junction Temperature		TJ	-55 to +125	°C
Storage Temperature	T _{stg}	-55 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

http://onsemi.com





SC-88 / SOT-363 CASE 419B STYLE 6

MARKING DIAGRAM



xx = Device Code

Refer to Ordering Table,

page 2

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I _R = 10 μA)	MBD110DWT1 MBD330DWT1 MBD770DWT1	V _{(BR)R}	7.0 30 70	10 - -		V
Diode Capacitance (V _R = 0, f = 1.0 MHz, Note 1)	MBD110DWT1	C _D	_	0.88	1.0	pF
Total Capacitance (V _R = 15 Volts, f = 1.0 MHz) (V _R = 20 Volts, f = 1.0 MHz)	MBD330DWT1 MBD770DWT1	C _T	-	0.9 0.5	1.5 1.0	pF
Reverse Leakage (V _R = 3.0 V) (V _R = 25 V) (V _R = 35 V)	MBD110DWT1 MBD330DWT1 MBD770DWT1	I _R	- - -	0.02 13 9.0	0.25 200 200	μΑ nA nA
Noise Figure (f = 1.0 GHz, Note 2)	MBD110DWT1	NF	_	6.0	_	dB
Forward Voltage (I _F = 10 mA) (I _F = 1.0 mA)	MBD110DWT1 MBD330DWT1 MBD770DWT1	V _F		0.5 0.38 0.52 0.42 0.7	0.6 0.45 0.6 0.5 1.0	V

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MBD110DWT1		SC-88 / SOT-363	
MBD110DWT1G	M4	SC-88 / SOT-363 (Pb-Free)	
MBD330DWT1		SC-88 / SOT-363	
MBD330DWT1G	T4	SC-88 / SOT-363 (Pb-Free)	3000 Units / Tape & Reel
MBD770DWT1		SC-88 / SOT-363	
MBD770DWT1G	H5	SC-88 / SOT-363 (Pb-Free)	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS MBD110DWT1

100

10

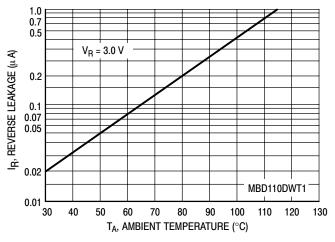


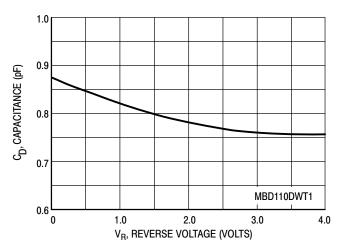
Figure 1. Reverse Leakage

V_F, FORWARD VOLTAGE (VOLTS)

Figure 2. Forward Voltage

LOCAL OSCILLATOR FREQUENCY = 1.0 GHz

0.8



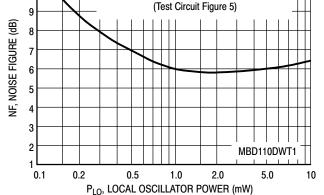


Figure 3. Capacitance

Figure 4. Noise Figure

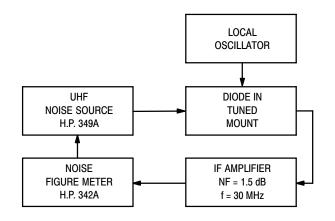
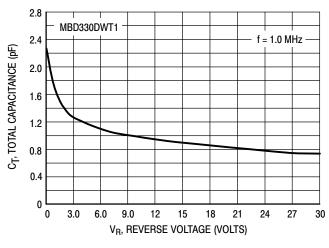


Figure 5. Noise Figure Test Circuit

NOTES ON TESTING AND SPECIFICATIONS

- Note 1 C_D and C_T are measured using a capacitance bridge (Boonton Electronics Model 75A or equivalent).
- Note 2 Noise figure measured with diode under test in tuned diode mount using UHF noise source and local oscillator (LO) frequency of 1.0 GHz. The LO power is adjusted for 1.0 mW. IF amplifier NF = 1.5 dB, f = 30 MHz, see
- Note 3 L_S is measured on a package having a short instead of a die, using an impedance bridge (Boonton Radio Model 250A RX Meter).

TYPICAL CHARACTERISTICS MBD330DWT1



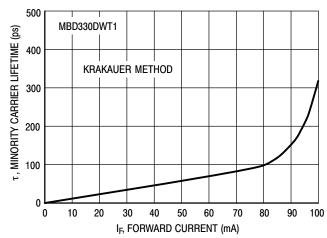
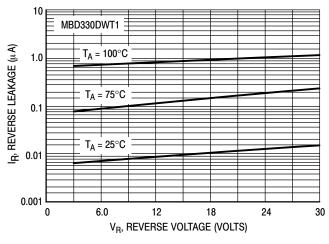


Figure 6. Total Capacitance

Figure 7. Minority Carrier Lifetime



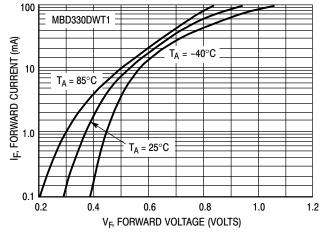
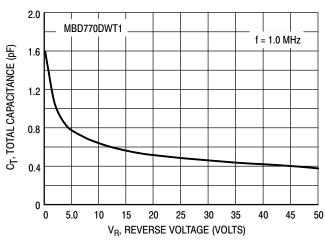


Figure 8. Reverse Leakage

Figure 9. Forward Voltage

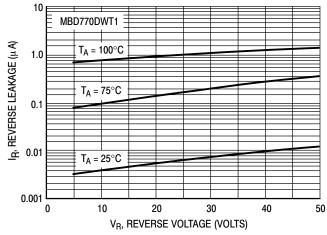
TYPICAL CHARACTERISTICS MBD770DWT1



(8) MBD770DWT1 WBD770DWT1 WBD770DWT1 100 KRAKAUER METHOD 100 100 20 30 40 50 60 70 80 90 100 I_F, FORWARD CURRENT (mA)

Figure 10. Total Capacitance

Figure 11. Minority Carrier Lifetime





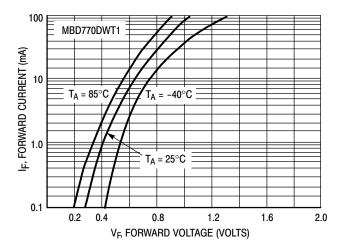
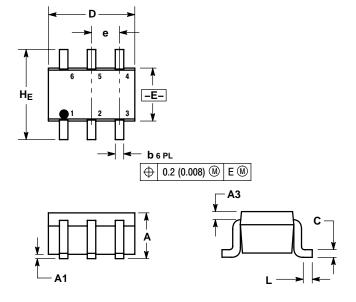


Figure 13. Forward Voltage

PACKAGE DIMENSIONS

SC-88 / SC-70 / SOT-363 CASE 419B-02 ISSUE W



NOTES

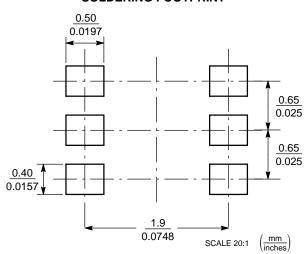
- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14 5M 1982
- CONTROLLING DIMENSION: INCH.
- 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.80	0.95	1.10	0.031	0.037	0.043	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
А3		0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012	
U	0.10	0.14	0.25	0.004	0.005	0.010	
ם	1.80	2.00	2.20	0.070	0.078	0.086	
Е	1.15	1.25	1.35	0.045	0.049	0.053	
е	0.65 BSC			0	.026 BS	С	
Ĺ	0.10	0.20	0.30	0.004	0.008	0.012	
He	2.00	2.10	2.20	0.078	0.082	0.086	

STYLE 6: PIN 1. ANODE 2

- N/C
- CATHODE 1 ANODE 1

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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